Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4140T-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · General-purpose switching and muting
- LCD backlighting
- Supply line switching circuits
- · Battery-driven equipment (mobile phones, video cameras and handheld devices)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	300	500	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		C
3	С	collector		В—
			1 2	E sym132
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5140T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5140T-Q	%2Н

[1] % = placeholder for manufacturing site code

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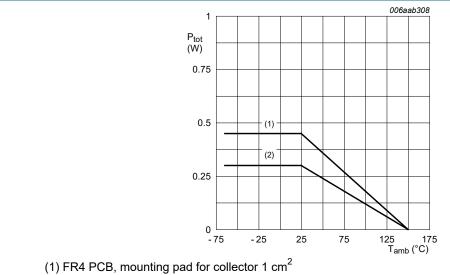
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-40	V
V_{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	Α
I _{BM}	peak base current			-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	450	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 $\rm cm^2$.



- (2) FR4 PCB, standard footprint

Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
11(J-a)	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	278	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

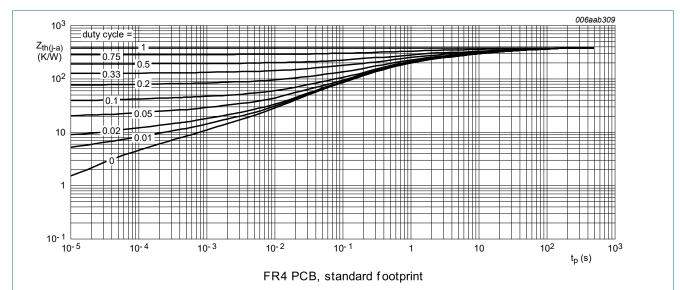


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

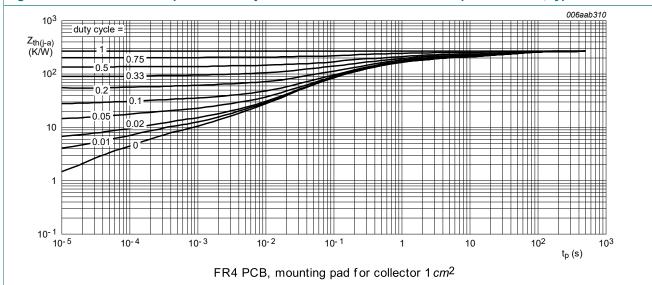


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
current		V _{CB} = -40 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CEO}	collector-emitter cut-off current (base open)	I _B = 0 A; V _{CE} = -30 V; T _{amb} = 25 °C	-	-	-100	nA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -1 mA; T _{amb} = 25 °C	300	-	-	
		V _{CE} = -5 V; I _C = -100 mA; T _{amb} = 25 °C	300	-	800	
		V_{CE} = -5 V; I_{C} = -500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$; T_{amb} = 25 °C	250	-	-	
		V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	160	-	-	
V _{CEsat} collector-emitter saturation voltage		I _C = -100 mA; I _B = -1 mA; T _{amb} = 25 °C	-	-	-200	mV
	saturation voltage	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-250	mV
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-500	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	300	500	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C	-	-	-1	V
t_d	delay time	V _{CC} = -10 V; I _C = -0.5 A; I _{Bon} = -25 mA;	-	10	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-	31	-	ns
t _{on}	turn-on time		-	41	-	ns
t _s	storage time		-	195	-	ns
t _f	fall time		-	65	-	ns
t _{off}	turn-off time		-	260	-	ns
f _T	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	12	pF

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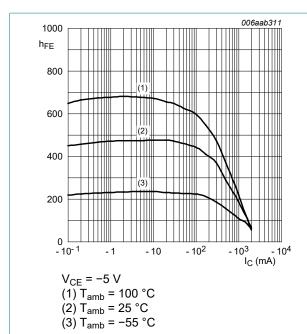


Fig. 4. DC current gain as a function of collector current; typical values

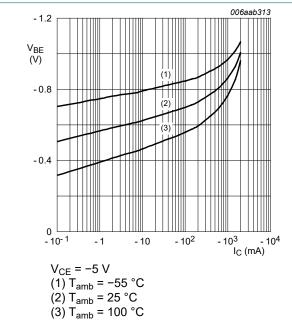


Fig. 6. Base-emitter voltage as a function of collector current; typical values

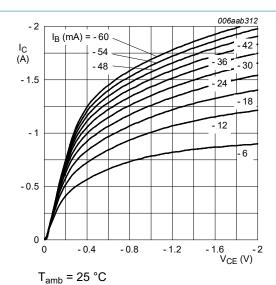
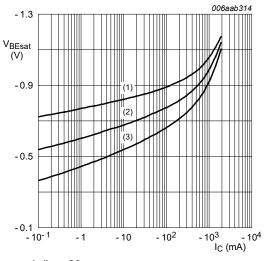


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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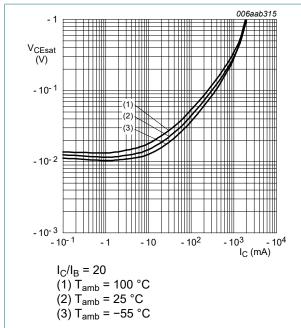


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

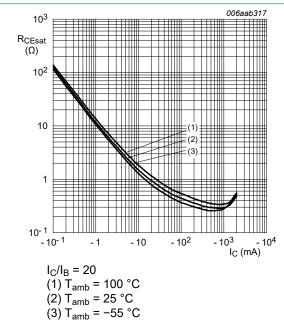


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

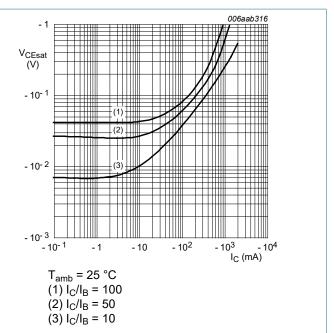


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

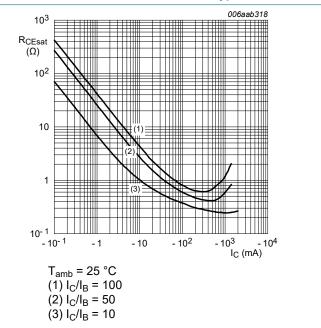
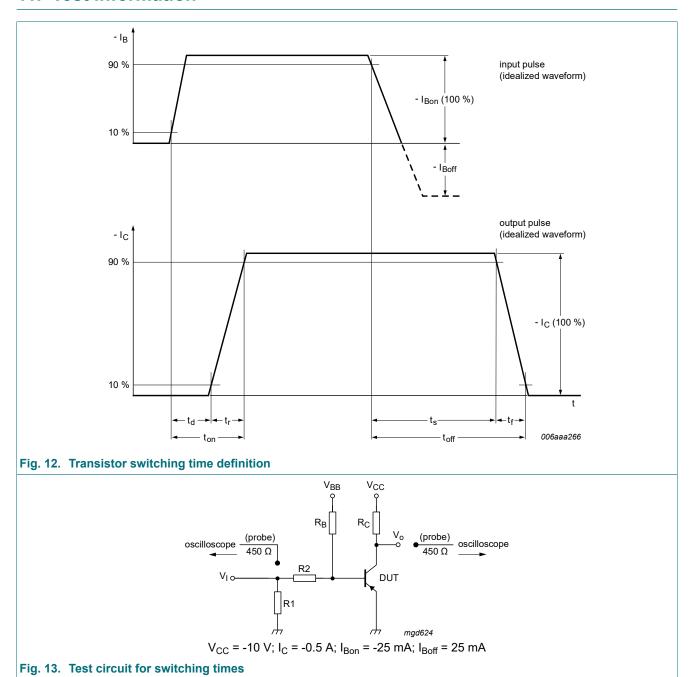


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

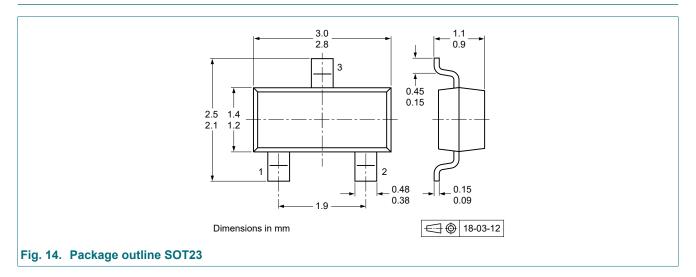


Quality information

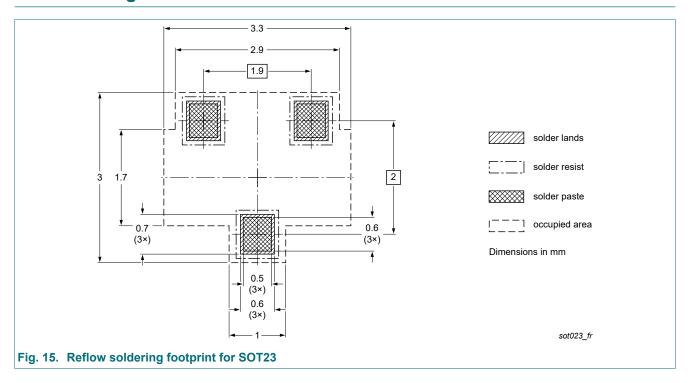
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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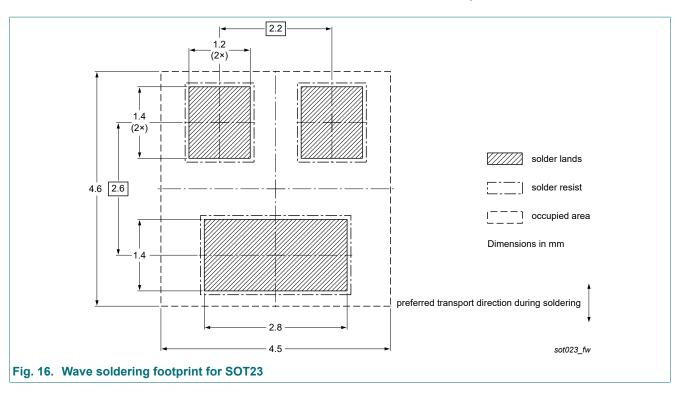
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5140T-Q v.1	20231004	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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